

GTVA107001EC/FC

High Power RF GaN on SiC HEMT 700 W, 50 V, DC - 1.4 GHz

Description

The GTVA107001EC and GTVA107001FC are 700-watt GaN on SiC high electron mobility transistors (HEMT) for use in the DC - 1.4 GHz frequency band.





Package Types: H-36248-2 PN's: GTVA107001EC

Package Types: H-37248-2 PN's: GTVA107001FC

Features

- GaN on SiC HEMT technology
- Input matched
- Typical pulsed CW performance (class AB), 1030 MHz, 50 V, 128 µs pulse width, 10% duty cycle
 - Output power P_{3dB} = 890 W
 - Drain efficiency = 75%
 - Gain = 18 dB
- Capable of withstanding a 10:1 load mismatch all phase angles at 700 W peak power under pulse conditions: 50 V, 100 mA I_{no} , 128 µs pulse width, 10% duty cycle
- Human body model class IC (per ANSI/ESDA/JEDEC JS-001)
- Pb-free and RoHS-compliant

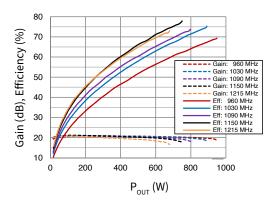


Figure 1. Power Sweep, Pulsed CW V_{DS} = 50 V, I_{DQ} = 100 mA, 128 μs Pulse Width, 10% Duty Cycle, Power Optimized

RF Characteristics

Pulsed RF performance (tested in the production test fixture)

GTVA107001EC: $V_{DD} = 50 \text{ V}$, $I_{DO} = 100 \text{ mA}$, $P_{OUT} = 700 \text{ W}$, f = 1030 MHz, 128 μ s pulse width, 10% duty cycle

Characteristic	Symbol	Min.	Тур.	Max.	Unit	
Gain	G_{ps}	17.5	20	22	dB	
Drain Efficiency	$\eta_{\scriptscriptstyle D}$	67	70	-	%	

GTVA107001FC: $V_{DD} = 50 \text{ V}$, $I_{DO} = 100 \text{ mA}$, $P_{OUT} = 700 \text{ W}$, f = 1030 MHz, 128 μ s pulse width, 10% duty cycle

Characteristic	cteristic Symbol		Тур.	Max.	Unit	
Gain	G_{ps}	17.5	20	22	dB	
Drain Efficiency	$\eta_{_{\mathrm{D}}}$	67	70	_	%	

All published data at T_{CASE} = 25 °C unless otherwise indicated

ESD: Electrostatic discharge sensitive device—observe handling precautions!



DC Characteristics

Characteristics	Conditions	Symbol	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{GS} = -8 \text{ V, } I_{D} = 10 \text{ mA}$	V _{(BR)DSS}	150	-	-	V
Drain-Source Leakage Current	$V_{GS} = -8 \text{ V}, V_{DS} = 10 \text{ V}$	I _{DSS}	-	-	12	mA
Gate Threshold Voltage	$V_{DS} = 10 \text{ V, } I_{D} = 84 \text{ mA}$	$V_{\rm GS(th)}$	-6.2	-3.0	-2.2	V

Recommended Operating Conditions

Parameter	Conditions	Symbol	Min.	Тур.	Max.	Unit
Drain Operating Voltage		V _{DD}	0	-	50	V
Gate Quiescent Voltage	$V_{DS} = 50 \text{ V}, I_{D} = 0.10 \text{ A}$	$V_{GS(Q)}$	-	-3.2	-	V

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit		
Drain-Source Voltage	$V_{\scriptscriptstyle DSS}$	125	V		
Gate-Source Voltage	V_{GS}	-10 to +2	V		
Gate Current	I _G	100	mA		
Drain Current	I _D	10	A		
Junction Temperature	T _J	225	°C		
Storage Temperature Range	T _{stg}	-65 to +150	°C		

Operation above the maximum values listed here may cause permanent damage. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the component. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. For reliable continuous operation, the device should be operated within the operating voltage range (V_{DD}) specified above.

Thermal Characteristics

Parameter	Symbol	Value	Unit	
Thermal Resistance, Junction to Case ¹	$R_{\theta JC}$	0.21	°C/W	
Thermal Resistance, Junction to Case ²	$R_{\theta JC}$	0.25	°C/W	

Ordering Information

Type and Version Order Code		Package and Description	Shipping
GTVA107001EC V1 R0	GTVA107001EC-V1-R0	H-36248-2, Bolt-Down Flange	Tape & Reel, 50 pcs
GTVA107001EC V1 R2	GTVA107001EC-V1-R2	H-36248-2, Bolt-Down Flange	Tape & Reel, 250 pcs
GTVA107001FC V1 R0	GTVA107001FC-V1-R0	H-37248-2, Earless Flange	Tape & Reel, 50 pcs
GTVA107001FC V1 R2	GTVA107001FC-V1-R0	H-37248-2, Earless Flange	Tape & Reel, 250 pcs

 $^{^1}$ T $_{CASE}$ = 85 °C, P $_{DISS}$ = 334 W, 50 V, I $_{DQ}$ = 100 mA, 128 μs pulse width, 10% duty cycle. 2 T $_{CASE}$ = 85 °C, P $_{DISS}$ = 254 W, 50 V, I $_{DQ}$ = 100 mA, Mode-S signal.



Typical Performance (Data Taken in the Production Test Fixture)

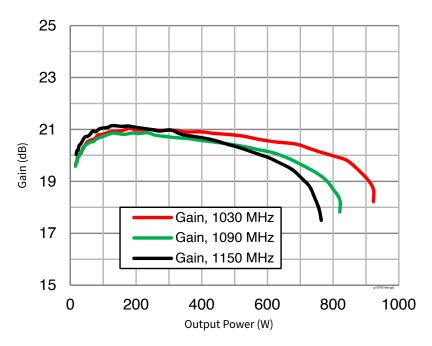


Figure 2. Power Sweep: Gain vs Output Power (Series Show Gain at Frequency) V_{DS} = 50 V, I_{DO} = 100 mA, 128 μs Pulse Width, 10% Duty Cycle, Power Optimized

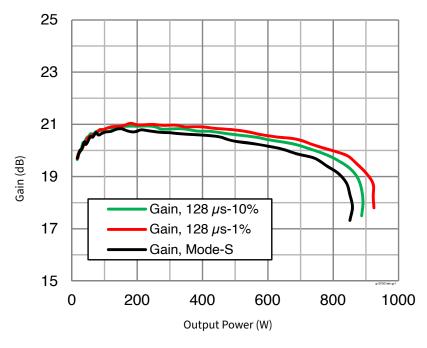


Figure 3. Power Sweep: Gain vs Output Power (Series Show Gain at Various Duty Cycles) $V_{DS} = 50 \text{ V}, I_{DO} = 100 \text{ mA}, f = 1030 \text{ MHz}$

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Typical Performance (Data Taken in the Production Test Fixture)

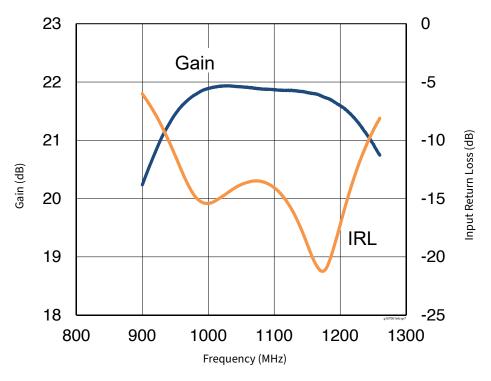


Figure 4. CW Performance Small Signal Gain & Input Return Loss $V_{DD} = 50 \text{ V}, I_{DO(MAIN)} = 1000 \text{ mA}$

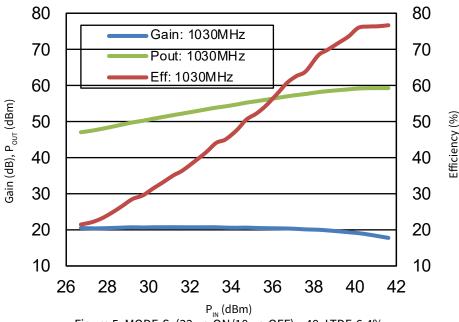


Figure 5. MODE-S: (32 μ s-ON/18 μ s-OFF) x 48, LTDF-6.4% V_{DS} = 50 V, I_{DQ} = 100 mA, Measured on 24th Pulse



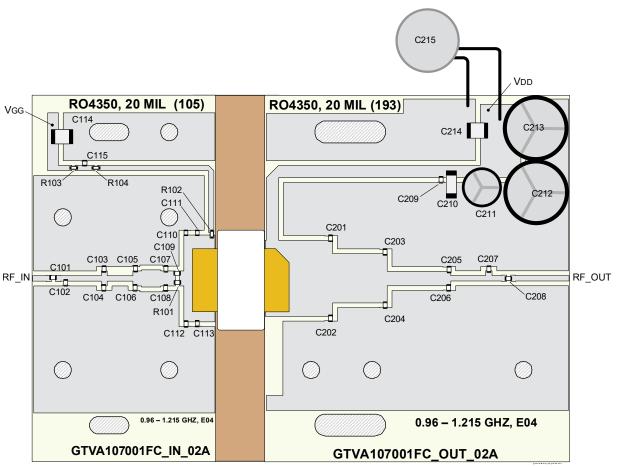
Load Pull Performance

Each side load pull performance –16 μs pulse width, 10% duty cycle, class AB, V_{DD} = 50 V, 60 mA

	Max Output Power			Max Efficiency				Z Optimum								
Freq [MHz]	Р _{оит} [dBm]	Р _{оит} [W]	Eff. [%]	Gain [dB]	Z_{Load} $[\Omega]$	Р _{оит} [dBm]	Р _{оит} [W]	Eff. [%]	Gain [dB]	Z_{Load} $[\Omega]$	Р _{оит} [dBm]	Р _{оит} [W]	Eff. [%]	Gain [dB]	Z_{Load} $[\Omega]$	$Z_{Source} [\Omega]$
960	60.37	1088.93	75.03	19.66	1.28+j0.10	59.43	877.00	83.15	20.84	1.37+j0.85	60.02	1004.62	79.99	20.45	1.28+j0.52	0.38-j1.05
1030	60.14	1032.76	74.45	19.58	1.28+j0.19	58.68	737.90	83.12	20.88	1.61+j1.01	60.01	1002.31	78.22	20.00	1.39+j0.43	0.43-j1.15
1090	59.88	972.75	73.06	19.08	1.32+j0.28	58.73	746.45	80.44	19.94	1.83+j0.97	59.70	933.25	77.40	19.53	1.48+j0.52	0.66-j1.27
1150	59.34	859.01	67.27	19.46	1.51+j0.13	58.30	676.08	77.38	20.91	1.72+j1.07	59.21	833.68	72.17	20.07	1.59+j0.46	0.81-j1.44
1200	59.20	831.76	66.29	19.34	1.54+j0.11	58.12	648.63	75.83	20.09	2.19+j0.97	59.09	810.96	70.51	19.79	1.68+j0.33	1.00-j1.73
1215	59.02	797.99	65.34	19.44	1.59+j0.01	57.74	594.29	73.93	20.63	2.02+j1.07	58.94	783.43	70.07	19.97	1.70+j0.33	1.55-j1.60

Reference Circuit Tuned for 0.960 to 1.215 GHz

DUT	GTVA107001EC V1 or GTVA107001FC V1
Reference Circuit Part No.	LTN/GTVA107001FC V1 or LTN/GTVA107001FC V1
PCB	Rogers 4350, 0.508 mm [.020"] Thick , 2 oz. Copper, ε_{r} = 3.66



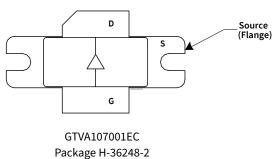
Reference circuit assembly diagram (not to scale)



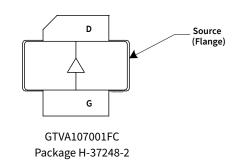
Reference Circuit (Cont.)

Components Informatio				
Component	Description	Manufacturer	P/N	
Input				
C101, C109, C115	Capacitor, 56 pF	ATC	ATC800A560JT250XT	
C102	Capacitor, 0.4 pF	ATC	ATC600F0R4AT250XT	
C103, C104	Capacitor, 1 pF	ATC	ATC600F1R0BT250XT	
C105	Capacitor, 3.6 pF	ATC	ATC600F3R6BT250XT	
C106	Capacitor, 3.3 pF	ATC	ATC600F3R3BT250XT	
C107, C108	Capacitor, 0.2 pF	ATC	ATC600F0R2AT250XT	
C110, C112, C113	Capacitor, 5.6 pF	ATC	ATC600F5R6BT250XT	
C111	Capacitor, 6.8 pF	ATC	ATC600F6R8BT250XT	
C114	Capacitor, 1 μF	TDK Corporation	C4532X7R2A105M230KA	
R101, R102	Resistor, 10 W	Panasonic – ECG	ERJ-3GEYJ100V	
R103	Resistor, 5.6 W	Panasonic – ECG	ERJ-8RQJ5R6V	
R104	Resistor, 100 W	Panasonic – ECG	ERJ-3GEYJ101V	
Output				
C201	Capacitor, 7.5 pF	ATC	ATC600F7R5BT250XT	
C202	Capacitor, 6.8 pF	ATC	ATC600F6R8BT250XT	
C203, C204	Capacitor, 2.4 pF	ATC	ATC600F2R4BT250XT	
C205, C206, C207	Capacitor, 1.5 pF	ATC	ATC600F1R5BT250XT	
C208	Capacitor, 39 pF	ATC	ATC600F390JT250XT	
C209	Capacitor, 56 pF	ATC	ATC800A560JT250XT	
C210	Capacitor, 10 μF	TDK Corporation	C5750X5R1H106K230KA	
C211	Capacitor, 22 μF	Cornell Dubilier Electronics (CDE)	SEK220M100ST	
C212	Capacitor, 100 μF	Cornell Dubilier Electronics (CDE)	SK101M100ST	
C213	Capacitor, 220 μF	Panasonic – ECG	ECA-2AHG221	
C214	Capacitor, 1 μF	TDK Corporation	C4532X7R2A105M230KA	
C215	Capacitor, 100 V, 6800 μF	Panasonic – ECG ECO-S2AP682E		

Pinout Diagrams (Top View)

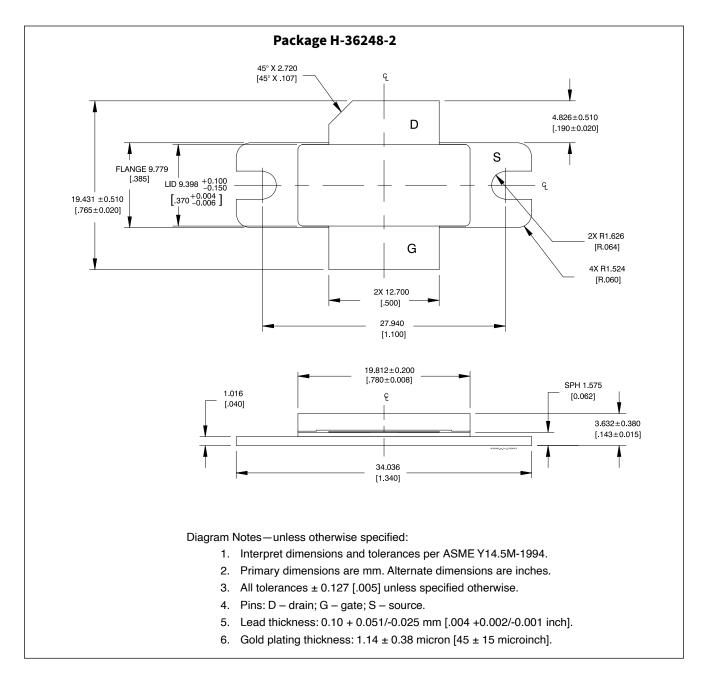


Pin	Description
D	Drain
G	Gate
S	Source (Flange)



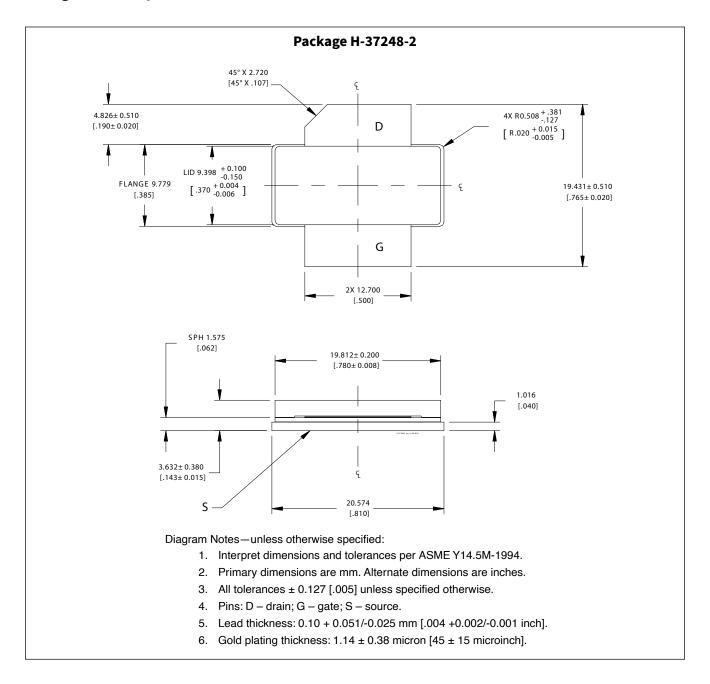


Package Outline Specifications





Package Outline Specifications





Revision History

Revision	Date	Data Sheet Type	Page	Subjects (Major Changes at Each Revision)
01	2016-09-27	Advance	All	Data Sheet Reflects Advance Specification for Product Development
02	2018-05-21	Preliminary	All	Data Sheet Shows Typical Performance Information and Reference Circuit
			All	Data Sheet Reflects Released Product Specification
02.1 2018-07-19	Production	1,3	Updated Typ Pulsed CW Performance, Added Mode S Graph	
02.12	2010 07 13	rioddedon	4	Added Loadpull Information, Added C215 to Reference Circuit and Component List
02.2	2018-10-02	Production	2	Updated Thermal Characteristics
03	2019-02-15	Production	All	Add Product GTVA107001FC V1
3.1	2021-10-14	Production	1	Removed "Thermally-Enhanced" Wording



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